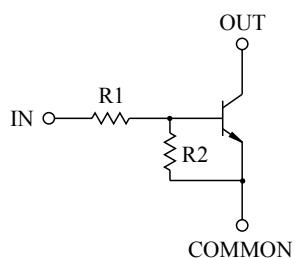


NPN Transistors

KRC107S ~ KRC109S

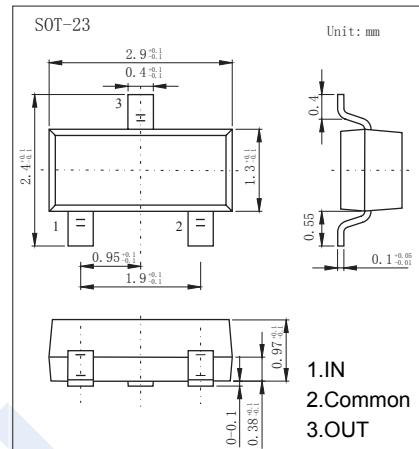
■ Features

- With Built in Bias Resistors
- Simplify Circuit Design
- Reduce a Quantity of Parts and Manufacturing Process
- Digital Transistors



BIAS RESISTOR VALUES

TYPE NO.	R1(kΩ)	R2(kΩ)
KRC107S	10	47
KRC108S	22	47
KRC109S	47	22



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Output Voltage	Vo	50	V
Input Voltage	KRC107S	30,-6	
	KRC108S	40,-7	
	KRC109S	40,-15	
Output Current	Io	100	mA
Power Dissipation	Pd	200	mW
Junction Temperature	Tj	150	°C
Storage Temperature Range	Tstg	-55 to 150	

NPN Transistors**KRC107S ~ KRC109S**

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Output Voltage	Vo(ON)	Io= 10mA, Ii= 0.5mA			0.3	V
Input Voltage (ON)	KRC107S	Vi(ON) Vo= 200 mV, Io= 5mA			1.8	
	KRC108S				2.6	
	KRC109S				5.8	
Input Voltage (OFF)	KRC107S	Vi(OFF) Vo= 5 V, Io= 0.1mA	0.5			mA
	KRC108S		0.6			
	KRC109S		1.5			
Output Cut-off Current	Io(OFF)	Vo= 50 V, Vi= 0			500	nA
Input Current	KRC107S	Ii Vi = 5V			0.88	mA
	KRC108S				0.36	
	KRC109S				0.16	
DC current gain	KRC107S	hFE Vo= 5V, Io= 10mA	80			us
	KRC108S		80			
	KRC109S		70			
Rise Time	KRC107S	trr			0.05	us
	KRC108S				0.12	
	KRC109S				0.26	
Storage Time	KRC107S	tstg Vo=5V,VIN=5V,RL=1KΩ			2	us
	KRC108S				2.4	
	KRC109S				1.5	
Fall Time	KRC107S	tf			0.36	us
	KRC108S				0.4	
	KRC109S				0.41	
Transition frequency	fT	Vo= 10V, Io= 5 mA			200	MHz

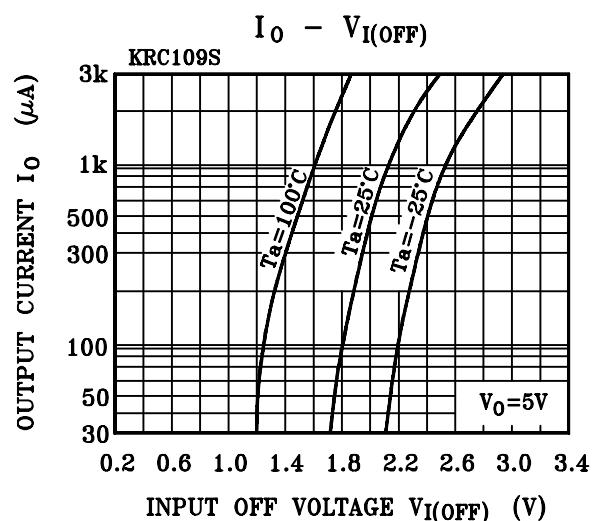
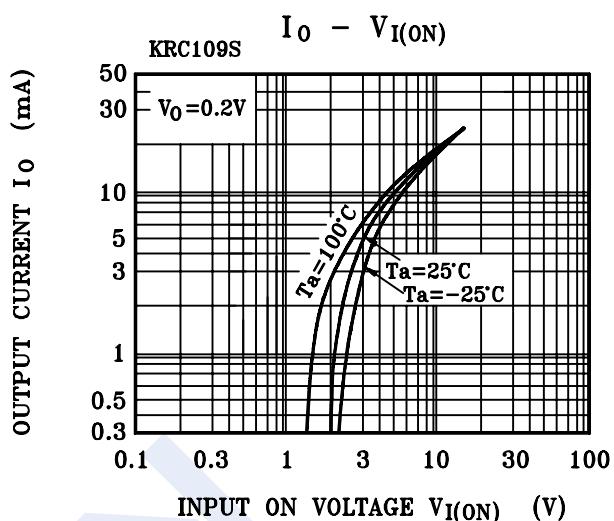
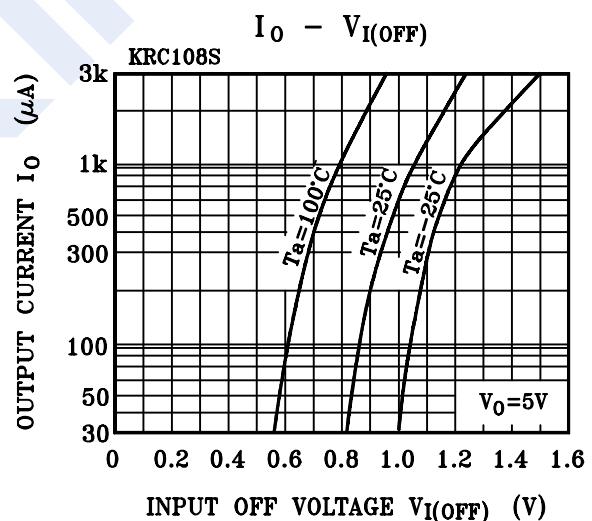
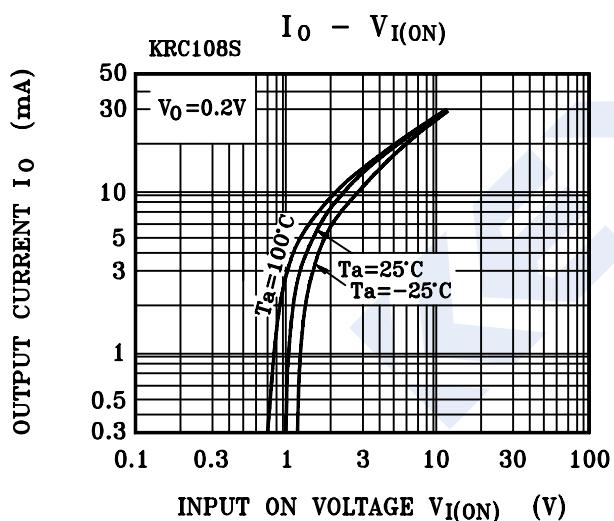
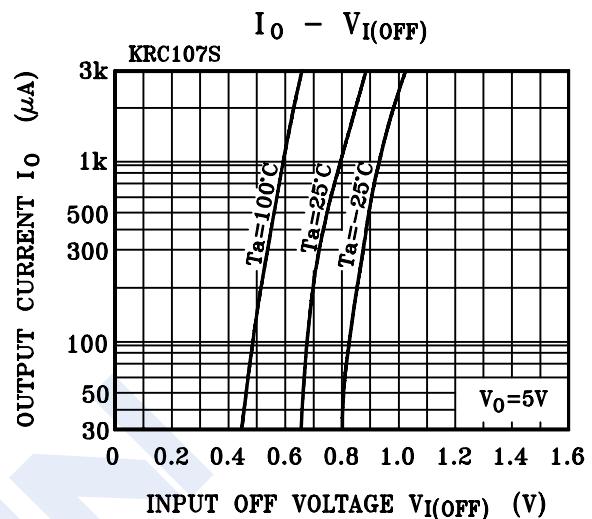
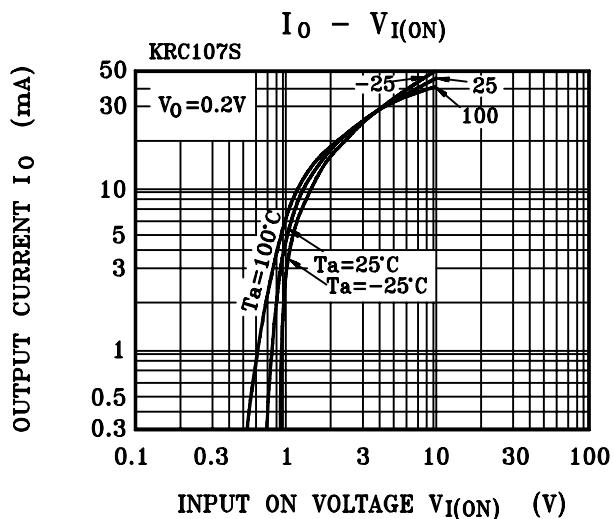
■ Marking

No	KRC107S	KRC108S	KRC109S
Marking	NH	NI	NJ

NPN Transistors

KRC107S ~ KRC109S

■ Typical Characteristics



NPN Transistors**KRC107S ~ KRC109S**

■ Typical Characteristics

